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November 2013

# FCB36N60N N-Channel SupreMOS<sup>®</sup> MOSFET

600 V, 36 A, 90 mΩ

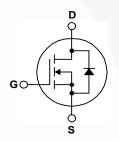
# **Features**

- R<sub>DS(on)</sub> = 81 mΩ (Typ.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 18 A
- Ultra Low Gate Charge (Typ. Qg = 86 nC)
- Low Effective Output Capacitance (Typ. C<sub>oss(eff.)</sub> = 361 pF)
- 100% Avalanche Tested
- · RoHS Compliant

# Applications

- Solar Inverter
- AC-DC Power Supply





The SupreMOS® MOSFET is Fairchild Semiconductor's next

generation of high voltage super-junction (SJ) technology

employing a deep trench filling process that differentiates it from

the conventional SJ MOSFETs. This advanced technology and

precise process control provides lowest Rsp on-resistance,

superior switching performance and ruggedness. SupreMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV

power, ATX power, and industrial power applications.

Description

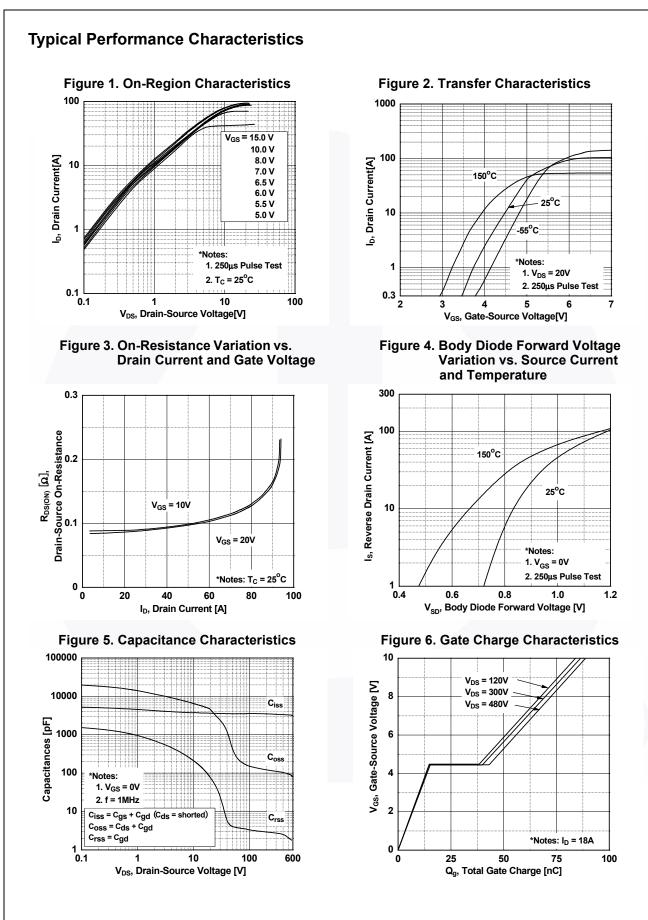
## MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter			FCB36N60N	Unit
V <sub>DSS</sub>	Drain to Source Voltage			600	V
V <sub>GSS</sub>	Gate to Source Voltage			±30	V
	Drain Current	- Continuous (T <sub>C</sub> = 25 <sup>o</sup> C)		36	
I <sub>D</sub>		- Continuous (T <sub>C</sub> = 100 <sup>o</sup> C)		22.7	- A
I <sub>DM</sub>	Drain Current	- Pulsed (Note 1)		108	А
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)			1800	mJ
I <sub>AR</sub>	Avalanche Current (Note 1)			12	А
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)			3.12	mJ
dv/dt	MOSFET dv/dt			100	V/ns
Peak Diode Recovery dv/dt		(	Note 3)	20	V/ns
P <sub>D</sub>	Dower Dissinction	$(T_{\rm C} = 25^{\rm o}{\rm C})$		312	W
	Power Dissipation	- Derate Above 25°C		2.6	W/ºC
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
ΤL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		s	300	°C

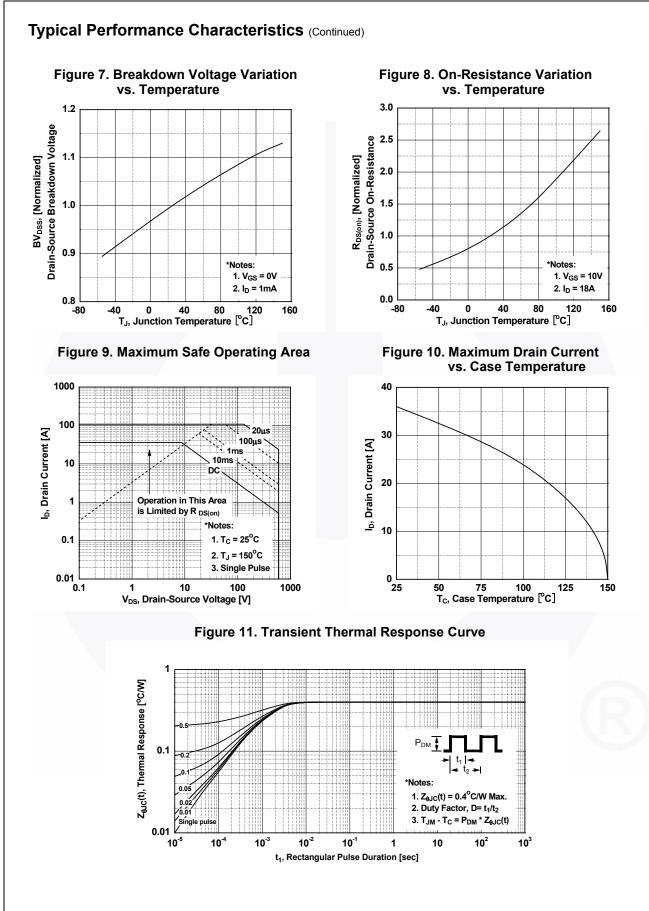
## **Thermal Characteristics**

Symbol	Parameter	FCB36N60N	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.4	
$R_{\thetaJA}$	$R_{\theta JA}$ Thermal Resistance, Junction to Ambient (1 in <sup>2</sup> Pad of 2-oz Copper), Max.		°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	]

Part Number Top Mark Pac		Packag	e Packing M	ethod	Reel Size	Tape Width		Qua	ntity	
FCB36N			D <sup>2</sup> -PAK	Tape and	Reel	330 mm	2	4 mm	800 units	
Electrica	l Chara	acteristics T <sub>C</sub> =:	25°C unless	otherwise noted						
Symbol	~			Test Conditions			Min.	Тур.	Max.	Unit
Off Charac	cteristics	;								
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage		ltage	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0 V, T <sub>C</sub> = 25 <sup>o</sup> C			600	-	-	V
ΔBV <sub>DSS</sub> /ΔTJ	Breakdown Voltage Temperature Coefficient		re	$I_D = 1$ mA, Referenced to $25^{\circ}C$			-	0.7	-	V/ºC
ı.	7000 004			V <sub>DS</sub> = 480 V, V <sub>GS</sub> = 0 V		-	-	10		
DSS	Zero Gat	Zero Gate Voltage Drain Current		$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, T_C = 125^{\circ}\text{C}$		-	-	100	μA	
I <sub>GSS</sub>	Gate to E	Body Leakage Current		V <sub>GS</sub> = ±30 V, V			-	-	±100	nA
On Charac	teristics	i								
V <sub>GS(th)</sub>	Gate Thr	reshold Voltage		$V_{GS} = V_{DS}, I_D$	= 250 μA		2.0	-	4.0	V
R <sub>DS(on)</sub>	Static Dr	ain to Source On Resi	stance	$V_{GS}$ = 10 V, $I_D$	= 18 A		-	81	90	mΩ
9 <sub>FS</sub>	Forward	Transconductance		V <sub>DS</sub> = 40 V, I <sub>D</sub> = 18 A		-	41	-	S	
Dynamic (	Characte	ristics								
C <sub>iss</sub>	T	pacitance		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, f = 1 MHz		-	3595	4785	pF	
C <sub>oss</sub>	Output C	apacitance				-	149	200	pF	
C <sub>rss</sub>	Reverse	Transfer Capacitance				-	4	6	pF	
C <sub>oss</sub>	Output Capacitance			V <sub>DS</sub> = 380 V, V <sub>GS</sub> = 0 V, f = 1 MHz			-	80	-	pF
C <sub>oss(eff.)</sub>	Effective	Output Capacitance		$V_{DS} = 0 V \text{ to } 380 V, V_{GS} = 0 V$		-	361	-	pF	
Q <sub>g(tot)</sub>	Total Gat	te Charge at 10V		V <sub>DS</sub> = 380 V, I <sub>D</sub> = 18 A, V <sub>GS</sub> = 10 V (Note 4) f = 1 MHz			-	86	112	nC
Q <sub>gs</sub>	Gate to S	Source Gate Charge				-	15.4	-	nC	
Q <sub>gd</sub>	Gate to D	Drain "Miller" Charge				-	26.4	-	nC	
ESR	Equivale	nt Series Resistance (	G-S)			-	1	-	Ω	
Switching	Charact	eristics								
t <sub>d(on)</sub>	Turn-On	Delay Time						23	56	ns
t <sub>r</sub>	Turn-On Rise Time			V <sub>DD</sub> = 380 V, I <sub>D</sub> = 18 A,		-	22	54	ns	
t <sub>d(off)</sub>	Turn-Off	Delay Time		$V_{GS} = 10 \text{ V}, \text{ R}_{G} = 4.7 \Omega$ (Note 4)		-	94	198	ns	
t <sub>f</sub>	Turn-Off	Fall Time				-	4	18	ns	
Drain-Sou	rce Diod	e Characteristics								
I <sub>S</sub>				e Forward Curre	nt		_	-	36	Α
I <sub>SM</sub>	Maximum Continuous Drain to Source Dio Maximum Pulsed Drain to Source Diode F					-	-	108	A	
V <sub>SD</sub>	Drain to Source Diode Forward Voltage			$V_{GS} = 0 V$ , $I_{SD} = 18 A$		-	- /	1.2	V	
t <sub>rr</sub>		Recovery Time	Vollago	$V_{GS} = 0.V, I_{SD} = 18 \text{ A}$ $V_{GS} = 0.V, I_{SD} = 18 \text{ A},$ $dI_{F}/dt = 100 \text{ A}/\text{\mu s}$		-	574	-	ns	
Q <sub>rr</sub>		Recovery Charge				-	10	-	μC	
an		receivery charge						10		μο



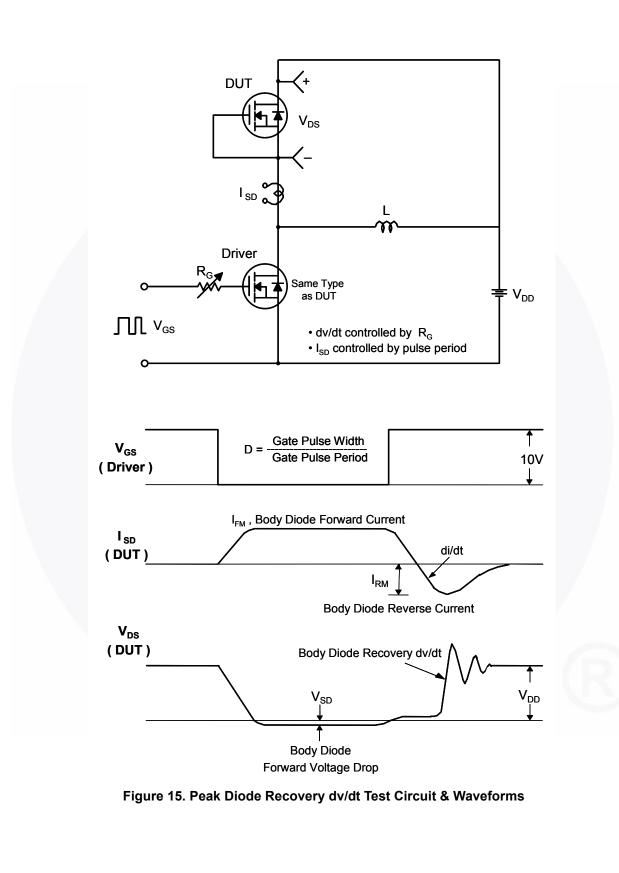
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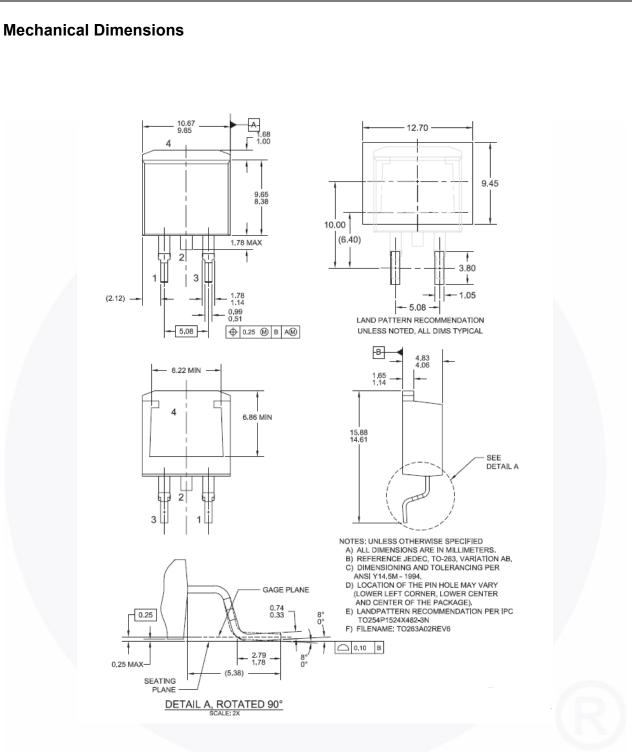


4

 $V_{GS}$ ξ א  $\mathsf{Q}_\mathsf{g}$ FV<sub>DS</sub>  $\mathsf{Q}_{\mathsf{gd}}$  $\mathsf{Q}_{\mathsf{gs}}$ • DUT I<sub>G</sub> = const. Charge Figure 12. Gate Charge Test Circuit & Waveform R VDS V<sub>DS</sub> 90% ο V<sub>DD</sub> GS  $\mathsf{R}_{\mathsf{G}}$ 10% V<sub>GS</sub> DUT V<sub>GS</sub> ∏ 0 Figure 13. Resistive Switching Test Circuit & Waveforms L  $E_{AS} = \frac{1}{2} L I_{AS}^2$ V<sub>DS</sub>  $\mathsf{BV}_{\mathsf{DSS}}$ ID o  $I_{AS}$  $R_{G}$ ŧν<sub>DD</sub>  $I_{D}(t)$  $\mathsf{V}_{\mathsf{D}\mathsf{D}}$ V<sub>GS</sub> ]  $V_{DS}(t)$ DUT Time t<sub>p</sub> Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

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# Figure 16. TO263 (D<sup>2</sup>PAK), Molded, 2-Lead, Surface Mount

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